

Bui Nguyen Quoc Trinh

List of Publications by Year in descending order

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173
citing authors

| # | ARTICLE | IF | CITATIONS |
|----|---|-----|-----------|
| 1 | Solution-processable zinc oxide based thin films with different aluminum doping concentrations. Journal of Science: Advanced Materials and Devices, 2020, 5, 497-501. | 3.1 | 2 |
| 2 | Solution-Processed Cupric Oxide P-type Channel Thin-Film Transistors. Thin Solid Films, 2020, 704, 137991. | 1.8 | 7 |
| 3 | Solution processed In-Si-O thin film transistors on hydrophilic and hydrophobic substrates. Thin Solid Films, 2020, 698, 137860. | 1.8 | 5 |
| 4 | Silicon-doped indium oxide " a promising amorphous oxide semiconductor material for thin-film transistor fabricated by spin coating method. IOP Conference Series: Materials Science and Engineering, 2019, 625, 012002. | 0.6 | 2 |
| 5 | Demonstration on Ferroelectric-gate Thin Film Transistor NAND-type Array with Disturbance-free Operation. VNU Journal of Science Mathematics - Physics, 2019, 35, . | 0.1 | 0 |
| 6 | Solution-processed CuO thin films with various Cu ²⁺ ion concentrations. Thin Solid Films, 2018, 660, 819-823. | 1.8 | 6 |
| 7 | Investigation on solution-processed In-Si-O thin-film transistor via spin-coating method. , 2018, , . | | 1 |
| 8 | Epitaxial-like growth of solution-processed PbZr _{0.4} Ti _{0.6} O ₃ thin film on single-crystal Nb-doped SrTiO ₃ substrate. VNU Journal of Science Mathematics - Physics, 2018, 33, . | 0.1 | 0 |
| 9 | INVESTIGATION ON STRUCTURAL AND FERROELECTRIC PROPERTIES OF Bi _{3.25} La _{0.75} Ti ₃ O ₁₂ THIN FILMS. Science and Technology, 2018, 54, 80. | 0.2 | 0 |
| 10 | STUDY ON ITO THIN FILMS PREPARED BY MULTI-ANNEALING TECHNIQUE. Science and Technology, 2018, 54, 136. | 0.2 | 0 |
| 11 | Conductive-perovskite LaNiO ₃ thin films prepared by using solution process for electrode application. VNU Journal of Science Mathematics - Physics, 2018, 34, . | 0.1 | 1 |
| 12 | Low-temperature PZT thin-film ferroelectric memories fabricated on SiO ₂ /Si and glass substrates. Journal of Science: Advanced Materials and Devices, 2016, 1, 75-79. | 3.1 | 16 |
| 13 | Sub-100Ånm Ferroelectric-Gate Thin-Film Transistor with Low-Temperature PZT Fabricated on SiO ₂ /Si Substrate. Ferroelectrics, Letters Section, 2015, 42, 65-74. | 1.0 | 0 |
| 14 | Fabrication of 120-nm-channel-length ferroelectric-gate thin-film transistor by nanoimprint lithography. Japanese Journal of Applied Physics, 2014, 53, 02BC14. | 1.5 | 4 |
| 15 | Switchable voltage control of the magnetic anisotropy in heterostructured nanocomposites of CoFe/NiFe/PZT. Journal of the Korean Physical Society, 2013, 63, 812-816. | 0.7 | 2 |
| 16 | Interface Charge Trap Density of Solution Processed Ferroelectric Gate Thin Film Transistor Using ITO/PZT/Pt Structure. Ferroelectrics, Letters Section, 2013, 40, 17-29. | 1.0 | 7 |
| 17 | Electric Properties and Interface Charge Trap Density of Ferroelectric Gate Thin Film Transistor Using (Bi,La) ₄ Ti ₃ O ₁₂ /Pb(Zr,Ti)O ₃ Stacked Gate Insulator. Japanese Journal of Applied Physics, 2012, 51, 09LA09. | 1.5 | 1 |
| 18 | Electric Properties and Interface Charge Trap Density of Ferroelectric Gate Thin Film Transistor Using (Bi,La) ₄ Ti ₃ O ₁₂ /Pb(Zr,Ti)O ₃ Stacked Gate Insulator. Japanese Journal of Applied Physics, 2012, 51, 09LA09. | 1.5 | 1 |

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|----|---|-----|-----------|
| 19 | Ferroelectric-Gate Thin-Film Transistor Fabricated by Total Solution Deposition Process. Japanese Journal of Applied Physics, 2011, 50, 04DD09. | 1.5 | 19 |
| 20 | Analysis on interface layer between Pt electrode and ferroelectric layer of solution-processed PZT capacitor. Materials Research Society Symposia Proceedings, 2011, 1368, 1. | 0.1 | 1 |
| 21 | Lanthanum Oxide Capping Layer for Solution-Processed Ferroelectric-Gate Thin-Film Transistors. Materials Research Society Symposia Proceedings, 2011, 1337, 117. | 0.1 | 0 |
| 22 | Totally solution-processed ferroelectric-gate thin-film transistor. Applied Physics Letters, 2010, 97, . | 3.3 | 36 |
| 23 | A low-temperature crystallization path for device-quality ferroelectric films. Applied Physics Letters, 2010, 97, . | 3.3 | 33 |
| 24 | Optimization of Pt and PZT Films for Ferroelectric-Gate Thin Film Transistors. Ferroelectrics, 2010, 405, 281-291. | 0.6 | 12 |
| 25 | Fabrication and characterization of a ferroelectric-gate FET With a ITO/PZT/SRO/Pt stacked structure. , 2010, , . | | 5 |
| 26 | Disturb-Free Writing Operation for Ferroelectric-Gate Field-Effect Transistor Memories With Intermediate Electrodes. IEEE Transactions on Electron Devices, 2009, 56, 3090-3096. | 3.0 | 1 |
| 27 | Synthesis of undoped and M-doped ZnO (M = Co, Mn) nanopowder in water using microwave irradiation. Journal of Physics: Conference Series, 2009, 187, 012020. | 0.4 | 10 |
| 28 | Nondestructive Readout of Ferroelectric-Gate Field-Effect Transistor Memory With an Intermediate Electrode by Using an Improved Operation Method. IEEE Transactions on Electron Devices, 2008, 55, 3200-3207. | 3.0 | 4 |
| 29 | Improvement of Nondestructive Readout of Ferroelectric Gate FET Memory with an Intermediate Electrode by using New Data Writing and Reading Methods. Applications of Ferroelectrics, IEEE International Symposium on, 2007, , . | 0.0 | 1 |
| 30 | Fabrication of Polycrystalline Ferroelectric Gate FET Memory with an Intermediate Electrode. Applications of Ferroelectrics, IEEE International Symposium on, 2006, , . | 0.0 | 1 |
| 31 | Operation of Ferroelectric Gate Field-Effect Transistor Memory with Intermediate Electrode using Polycrystalline Capacitor and Metalâ€“Oxideâ€“Semiconductor Field-Effect Transistor. Japanese Journal of Applied Physics, 2006, 45, 7341-7344. | 1.5 | 3 |
| 32 | Control of Preferential Orientation of Platinum Films on RuO ₂ /SiO ₂ /Si Substrates by Sputtering. Japanese Journal of Applied Physics, 2006, 45, 8810-8816. | 1.5 | 3 |
| 33 | Spin reorientation in ErCo ₁₀ âˆ™xFe _x Mo ₂ compounds. Physica B: Condensed Matter, 2003, 327, 262-265. | 2.7 | 1 |